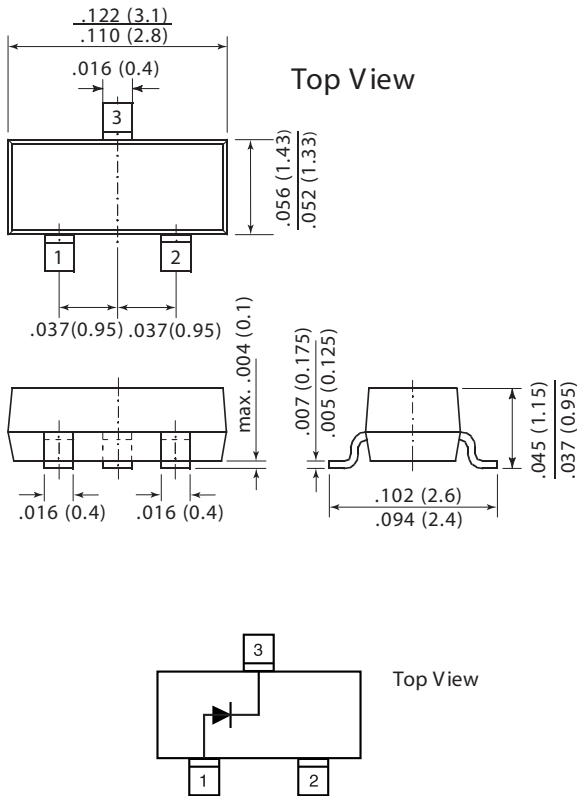


Features

SOT-23



- Silicon Epitaxial Planar Diode
- Fast switching diode in case SOT-23, especially suited for automatic insertion.

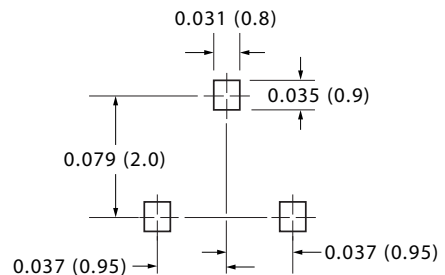
Mechanical Data

Case: SOT-23 Plastic Package

Weight: approx. 0.008g

Marking Code: A6

Mounting Pad Layout



Maximum Ratings and Thermal Characteristics (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	75	V
Peak Reverse Voltage	V _{RM}	100	V
Forward Current (continuous)	I _F	250	mA
Non-Repetitive Peak Forward Current	I _{FSM}	t = 1 μs □ 2.0	A
		t = 1 ms 1.0	
		t = 1 s 0.5	
Power Dissipation at T _{amb} = 25 °C	P _{tot}	350 ⁽¹⁾	mW
Thermal Resistance Junction to Ambient Air	R _{thJA}	430 ⁽¹⁾	°C/W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _s	-65 to +150	°C

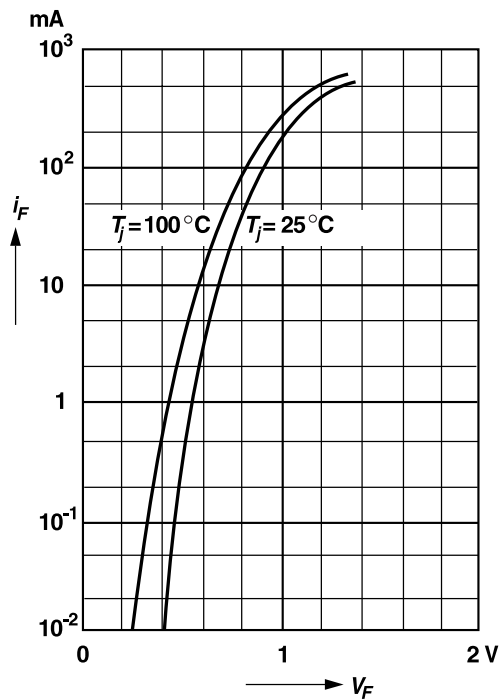
Note:

(1) Device on Fiberglass Substrate, see layout on second page

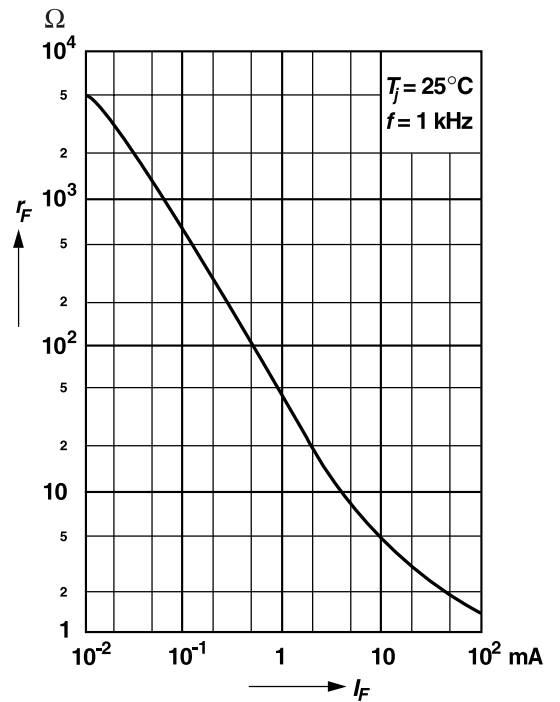
RATINGS AND CHARACTERISTIC CURVES BAS16

Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Forward characteristics

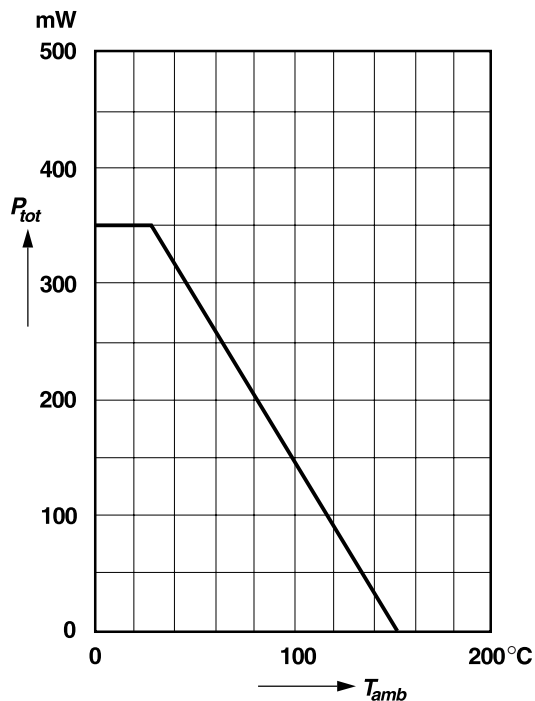


Dynamic forward resistance versus forward current

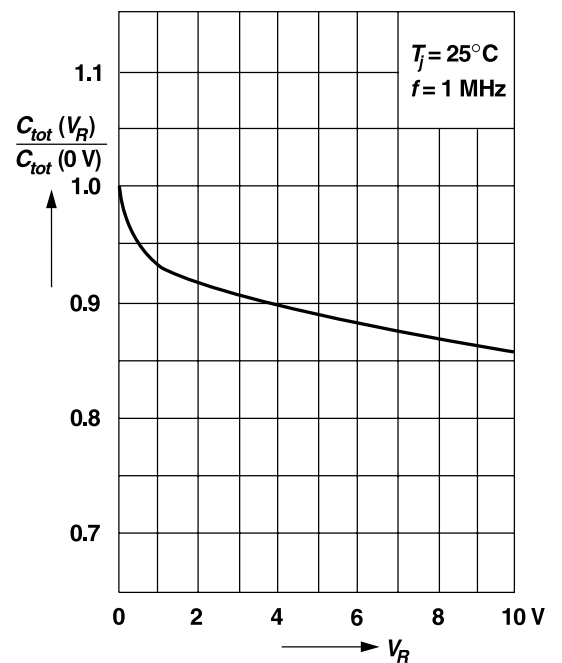


Admissible power dissipation versus ambient temperature

For conditions, see footnote in table "Absolute Maximum Ratings"

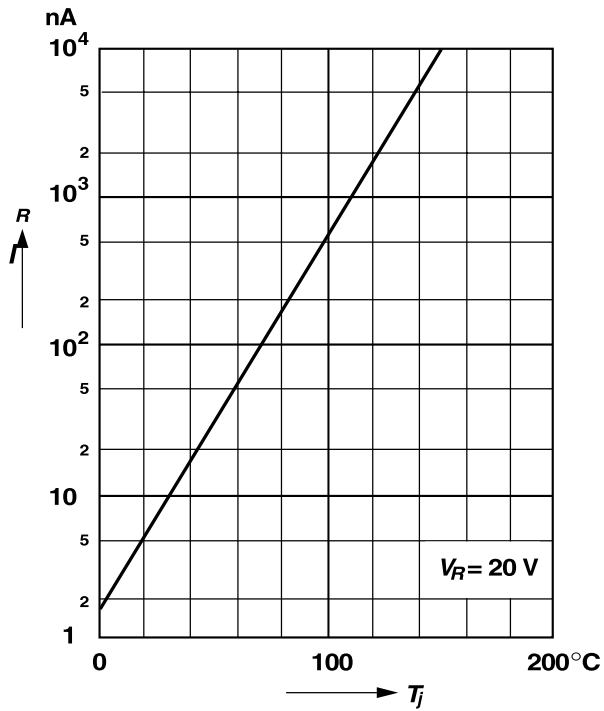


Relative capacitance versus reverse voltage



RATINGS AND CHARACTERISTIC CURVES BAS16

Leakage current versus junction temperature



Admissible repetitive peak forward current versus pulse duration

For conditions, see footnote in table "Absolute Maximum Ratings"

